

# Maciej Bugajski

## List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

128  
papers

1,100  
citations

18  
h-index

28  
g-index

153  
ext. papers

1,292  
ext. citations

2.2  
avg, IF

3.73  
L-index

| #   | Paper   | IF  | Citations |
|-----|---|-----|-----------|
| 128 | Coupled Cavity Mid-IR Quantum Cascade Lasers Fabricated by Dry Etching. <i>Photonics</i> , <b>2020</b> , 7, 45  | 2.2 | 2         |
| 127 | Optimization of MBE Growth Conditions of InAlAs Waveguide Layers for InGaAs/InAlAs/InP Quantum Cascade Lasers. <i>Materials</i> , <b>2019</b> , 12,   | 3.5 | 5         |
| 126 | Degradation of AlInAs/InGaAs/InP quantum cascade lasers due to electrode adhesion failure. <i>Microelectronics Reliability</i> , <b>2019</b> , 99, 113-118  | 1.2 | 1         |
| 125 | Coupled-cavity AlInAs/InGaAs/InP quantum cascade lasers fabricated by focused ion beam processing. <i>JPhys Photonics</i> , <b>2019</b> , 1, 015001   | 2.5 | 2         |
| 124 | Comparison of quantum cascade structures for detection of nitric oxide at ~ 5.2 $\mu$ m. <i>Optical and Quantum Electronics</i> , <b>2019</b> , 51, 1   | 2.4 | 3         |
| 123 | Optimization of Cavity Designs of Tapered AlInAs/InGaAs/InP Quantum Cascade Lasers Emitting at 4.5 $\mu$ m. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2019</b> , 25, 1-9   | 3.8 | 3         |
| 122 | Temperature induced degradation mechanisms of AlInAs/InGaAs/InP quantum cascade lasers. <i>Materials Research Express</i> , <b>2018</b> , 5, 016204   | 1.7 | 5         |
| 121 | Above room temperature operation of InGaAs/AlGaAs/GaAs quantum cascade lasers. <i>Semiconductor Science and Technology</i> , <b>2018</b> , 33, 035006   | 1.8 | 6         |
| 120 | Tuning quantum cascade laser wavelength by the injector doping. <i>Applied Physics B: Lasers and Optics</i> , <b>2018</b> , 124, 1  | 1.9 | 2         |
| 119 | Field distribution in waveguide of mid-infrared strain-compensated InAlAs/InGaAs/InP quantum cascade laser. <i>Optical and Quantum Electronics</i> , <b>2017</b> , 49, 1  | 2.4 | 1         |
| 118 | MBE growth of strain-compensated InGaAs/InAlAs/InP quantum cascade lasers. <i>Journal of Crystal Growth</i> , <b>2017</b> , 466, 22-29  | 1.6 | 19        |
| 117 | High-resolution mirror temperature mapping in GaN-based diode lasers by thermoreflectance spectroscopy. <i>Japanese Journal of Applied Physics</i> , <b>2017</b> , 56, 020302   | 1.4 | 5         |
| 116 | Numerical simulation of GaAs-based mid-infrared one-phonon resonance quantum cascade laser. <i>Optical and Quantum Electronics</i> , <b>2017</b> , 49, 1  | 2.4 | 5         |
| 115 | On the onset of strain relaxation in the Al <sub>0.45</sub> Ga <sub>0.55</sub> As/In <sub>x</sub> Ga <sub>1-x</sub> As active region in quantum cascade laser structures. <i>Journal of Applied Crystallography</i> , <b>2017</b> , 50, 1376-1381 | 3.8 | 5         |
| 114 | Characterization of the superlattice region of a quantum cascade laser by secondary ion mass spectrometry. <i>Nanoscale</i> , <b>2017</b> , 9, 17571-17575  | 7.7 | 8         |
| 113 | Examination of thermal properties and degradation of InGaN - based diode lasers by thermoreflectance spectroscopy and focused ion beam etching. <i>AIP Advances</i> , <b>2017</b> , 7, 075107   | 1.5 | 4         |
| 112 | Analysis of Free-Space Optics Development. <i>Metrology and Measurement Systems</i> , <b>2017</b> , 24, 653-674   |     | 24        |

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|-----|---|-----|----|
| 111 | Heat Dissipation Schemes in AlInAs/InGaAs/InP Quantum Cascade Lasers Monitored by CCD Thermoreflectance. <i>Photonics</i> , <b>2017</b> , 4, 47   | 2.2 | 6  |
| 110 | A novel method to calculate a near field of widely divergent laser beams. <i>Optical and Quantum Electronics</i> , <b>2016</b> , 48, 1  | 2.4 | 2  |
| 109 | High numerical aperture large-core photonic crystal fiber for a broadband infrared transmission. <i>Infrared Physics and Technology</i> , <b>2016</b> , 79, 10-16   | 2.7 | 7  |
| 108 | CCD thermoreflectance spectroscopy as a tool for thermal characterization of quantum cascade lasers. <i>Semiconductor Science and Technology</i> , <b>2016</b> , 31, 115006   | 1.8 | 16 |
| 107 | Optical examination of high contrast grating fabricated by focused-ion beam etching. <i>Optical and Quantum Electronics</i> , <b>2016</b> , 48, 1   | 2.4 |    |
| 106 | Single-mode enhancement in coupled-cavity quantum cascade lasers <b>2016</b> ,  |     | 1  |
| 105 | Optical Properties of Active Regions in Terahertz Quantum Cascade Lasers. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , <b>2016</b> , 37, 710-719   | 2.2 | 5  |
| 104 | Direct Au/Au bonding technology for high performance GaAs/AlGaAs quantum cascade lasers. <i>Optical and Quantum Electronics</i> , <b>2015</b> , 47, 893-899   | 2.4 | 11 |
| 103 | Monolithic high-index contrast grating: a material independent high-reflectance VCSEL mirror. <i>Optics Express</i> , <b>2015</b> , 23, 11674-86  | 3.3 | 33 |
| 102 | Impact of Injector Doping on Threshold Current of Mid-Infrared Quantum Cascade Laser Non-Equilibrium Green's Function Analysis. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , <b>2015</b> , 21, 124-133               | 3.8 | 10 |
| 101 | Room temperature, single mode emission from two-section coupled cavity InGaAs/AlGaAs/GaAs quantum cascade laser. <i>Journal of Applied Physics</i> , <b>2015</b> , 118, 133103  | 2.5 | 7  |
| 100 | Formation of coupled-cavities in quantum cascade lasers using focused ion beam milling. <i>Microelectronics Reliability</i> , <b>2015</b> , 55, 2142-2146   | 1.2 | 6  |
| 99  | Advanced optical characterization of AlGaAs/GaAs superlattices for active regions in quantum cascade lasers. <i>Optical and Quantum Electronics</i> , <b>2015</b> , 47, 945-952   | 2.4 | 5  |
| 98  | High-resolution X-ray characterization of mid-IR Al <sub>0.45</sub> Ga <sub>0.55</sub> As/GaAs Quantum Cascade Laser structures. <i>Thin Solid Films</i> , <b>2014</b> , 564, 339-344   | 2.2 | 5  |
| 97  | Mid-IR quantum cascade lasers: Device technology and non-equilibrium Green's function modeling of electro-optical characteristics (Phys. Status Solidi B 6/2014). <i>Physica Status Solidi (B): Basic Research</i> , <b>2014</b> , 251, | 1.3 | 1  |
| 96  | Time resolved FTIR study of spectral tuning and thermal dynamics of mid-IR QCLs <b>2014</b> ,   |     | 7  |
| 95  | Mid-IR quantum cascade lasers: Device technology and non-equilibrium Green's function modeling of electro-optical characteristics. <i>Physica Status Solidi (B): Basic Research</i> , <b>2014</b> , 251, 1144-1157                      | 1.3 | 25 |
| 94  | Room temperature AlInAs/InGaAs/inP quantum cascade lasers. <i>Photonics Letters of Poland</i> , <b>2014</b> , 6,  | 2.1 | 4  |

|    |   |     |    |
|----|---|-----|----|
| 93 | Multimode instabilities in mid-infrared quantum cascade lasers. <i>Photonics Letters of Poland</i> , <b>2013</b> , 5,   | 2.1 | 5  |
| 92 | Multi-step interrupted-growth MBE technology for GaAs/AlGaAs (~9.4 $\mu\text{m}$ ) room temperature operating quantum-cascade lasers. <i>Opto-electronics Review</i> , <b>2012</b> , 20,  | 2.4 | 6  |
| 91 | Investigation of thermal properties of mid-infrared AlGaAs/GaAs quantum cascade lasers. <i>Journal of Applied Physics</i> , <b>2012</b> , 112, 043112   | 2.5 | 30 |
| 90 | Nonthermal carrier distributions in the subbands of 2-phonon resonance mid-infrared quantum cascade laser. <i>Applied Physics Letters</i> , <b>2012</b> , 101, 061110   | 3.4 | 25 |
| 89 | High performance GaAs/AlGaAs quantum cascade lasers: optimization of electrical and thermal properties <b>2012</b> ,  |     | 4  |
| 88 | Experimental analysis of thermal properties of AlGaAs/GaAs quantum cascade lasers <b>2012</b> ,   |     | 4  |
| 87 | Optoelectronic properties of InAs/GaSb superlattices with asymmetric interfaces. <i>Journal of Physics: Conference Series</i> , <b>2012</b> , 367, 012014   | 0.3 | 0  |
| 86 | Electrical and optical characterisation of mid-IR GaAs/AlGaAs quantum cascade lasers <b>2012</b> ,  |     | 5  |
| 85 | Thermal effects in 2.x $\mu\text{m}$ vertical-external-cavity-surface-emitting lasers. <i>Journal of Applied Physics</i> , <b>2012</b> , 111, 053107  | 2.5 | 3  |
| 84 | AlGaAs/GaAs quantum cascade lasers for gas detection systems <b>2011</b> ,  |     | 1  |
| 83 | Determination of energy difference and width of minibands in GaAs/AlGaAs superlattices by using Fourier transform photoreflectance and photoluminescence. <i>Opto-electronics Review</i> , <b>2011</b> , 19,                          | 2.4 | 1  |
| 82 | The determination of the chemical composition profile of the GaAs/AlGaAs heterostructures designed for quantum cascade lasers by means of synchrotron radiation. <i>Radiation Physics and Chemistry</i> , <b>2011</b> , 80, 1112-1118 | 2.5 | 2  |
| 81 | Development of (~9.4 $\mu\text{m}$ ) GaAs-Based Quantum Cascade Lasers Operating at the Room Temperature. <i>NATO Science for Peace and Security Series B: Physics and Biophysics</i> , <b>2011</b> , 91-100                          | 0.2 | 2  |
| 80 | GaAs/AlGaAs (~9.4 $\mu\text{m}$ ) quantum cascade lasers operating at 260 K. <i>Bulletin of the Polish Academy of Sciences: Technical Sciences</i> , <b>2010</b> , 58,  |     | 3  |
| 79 | Influence of Operating Conditions on Quantum Cascade Laser Temperature. <i>Journal of Electronic Materials</i> , <b>2010</b> , 39, 630-634  | 1.9 | 7  |
| 78 | Quantification of thermoreflectance temperature measurements in high-power semiconductor devices lasers and laser bars. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 1373-1378   | 1.8 | 3  |
| 77 | Investigation of thermal management in optically pumped, antimonide VECSELs. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 558-561  | 1.8 | 8  |
| 76 | Molecular-beam epitaxy growth and characterization of mid-infrared quantum cascade laser structures. <i>Microelectronics Journal</i> , <b>2009</b> , 40, 565-569  | 1.8 | 17 |

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|----|---|-----|----|
| 75 | Low-temperature grown near surface semiconductor saturable absorber mirror: Design, growth conditions, characterization, and mode-locked operation. <i>Journal of Applied Physics</i> , <b>2009</b> , 106, 053101 | 2.5 | 6  |
| 74 | Development of (9.4 $\mu$ m) GaAs-based quantum cascade lasers <b>2009</b> ,  |     | 1  |
| 73 | Photoluminescence studies of optical properties of VECSEL active region under high excitation conditions. <i>Journal of Physics: Conference Series</i> , <b>2009</b> , 146, 012031                                | 0.3 | 1  |
| 72 | Molecular Beam Epitaxy Growth for Quantum Cascade Lasers. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, 806-813   | 3.6 | 5  |
| 71 | Mid-Infrared GaAs/AlGaAs Quantum Cascade Lasers Technology. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, S-45-S-47   | 11  |    |
| 70 | Electronic States in Type-II Superlattices. <i>Acta Physica Polonica A</i> , <b>2009</b> , 116, S-65-S-68   | 0.6 | 1  |
| 69 | Passively modelocked bi-directional vertical external ring cavity surface emitting laser <b>2008</b> ,  |     | 1  |
| 68 | Thermal processes in high-power laser bars investigated by spatially resolved thermoreflectance. <i>Journal of Materials Science: Materials in Electronics</i> , <b>2008</b> , 19, 150-154                        | 2.1 | 11 |
| 67 | The influence of the growth temperature and interruption time on the crystal quality of InGaAs/GaAs QW structures grown by MBE and MOCVD methods. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 2785-2792 | 1.6 | 17 |
| 66 | Characterization of (Al)GaAs/AlAs distributed Bragg mirrors grown by MBE and LP MOVPE techniques. <i>Journal of Crystal Growth</i> , <b>2008</b> , 310, 4094-4101   | 1.6 | 4  |
| 65 | Low-resistance p-type ohmic contacts for high-power InGaAs/GaAs-980 nm CW semiconductor lasers. <i>Vacuum</i> , <b>2008</b> , 82, 977-981   | 3.7 | 10 |
| 64 | Angular and Temperature Tuning of Emission from Vertical-External-Cavity Surface-Emitting Lasers (VECSELs). <i>Acta Physica Polonica A</i> , <b>2008</b> , 114, 1437-1443   | 0.6 |    |
| 63 | Facet Heating Mechanisms in High Power Semiconductor Lasers Investigated by Spatially Resolved Thermoreflectance <b>2007</b> ,  |     | 2  |
| 62 | Improvement of quantum efficiency of MBE grown AlGaAs/InGaAs/GaAs edge emitting lasers by optimisation of construction and technology. <i>Vacuum</i> , <b>2007</b> , 82, 383-388                                  | 3.7 | 1  |
| 61 | Thermal properties of high power laser bars investigated by spatially resolved thermoreflectance spectroscopy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2007</b> , 204, 422-429   | 1.6 | 6  |
| 60 | Tailoring of optical mode profiles of high-power diode lasers evidenced by near-field photocurrent spectroscopy. <i>Applied Physics Letters</i> , <b>2007</b> , 91, 101103  | 3.4 | 3  |
| 59 | Investigation of thermal processes in high power laser bars by thermoreflectance spectroscopy <b>2007</b> ,   |     | 1  |
| 58 | Thermoreflectance Measurements of the Temperature Distributions in Laser Diodes with Non Injected Facet. <i>Materials Research Society Symposia Proceedings</i> , <b>2006</b> , 916, 1                            |     | 2  |

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|----|--|-----|----|
| 57 | Complementary thermoreflectance and micro-Raman analysis of facet temperatures of diode lasers. <i>Applied Physics Letters</i> , <b>2006</b> , 89, 071104  | 3-4 | 35 |
| 56 | Room temperature photoluminescence studies of nitrided InP(100) surfaces. <i>Materials Science and Engineering C</i> , <b>2006</b> , 26, 378-382   | 8-3 |    |
| 55 | Investigation of oval defects in (In)Ga(Al)As/GaAs heterostructures by spatially resolved photoluminescence and micro-cathodoluminescence. <i>Materials Science in Semiconductor Processing</i> , <b>2006</b> , 9, 25-30   | 4-3 | 4  |
| 54 | Thermoreflectance study of facet heating in semiconductor lasers. <i>Materials Science in Semiconductor Processing</i> , <b>2006</b> , 9, 188-197  | 4-3 | 23 |
| 53 | Thermal properties of high-power diode lasers investigated by microthermography <b>2005</b> ,  |     | 5  |
| 52 | Advances in self-assembled semiconductor quantum dot lasers. <i>Microelectronics Journal</i> , <b>2005</b> , 36, 950-958   |     | 24 |
| 51 | Spatially resolved thermoreflectance study of facet temperature in quantum cascade lasers. <i>Physica Status Solidi (A) Applications and Materials Science</i> , <b>2005</b> , 202, 1227-1232  | 1.6 | 19 |
| 50 | Passivation of InP(100) substrates: first stages of nitridation by thin InN surface overlayers studied by electron spectroscopies. <i>Surface and Interface Analysis</i> , <b>2005</b> , 37, 615-620   | 1.5 | 3  |
| 49 | Analysis of thermal images from diode lasers: Temperature profiling and reliability screening. <i>Applied Physics Letters</i> , <b>2005</b> , 86, 203503   | 3-4 | 23 |
| 48 | Comprehensive self-consistent three-dimensional simulation of an operation of the GaAs-based oxide-confined 1.3- $\mu\text{m}$ quantum-dot (InGa)As/GaAs vertical-cavity surface-emitting lasers. <i>Optical and Quantum Electronics</i> , <b>2004</b> , 36, 331-347 | 2.4 | 17 |
| 47 | Analysis of Threshold Current and Wall-Plug Efficiency of Diode Lasers with Asymmetric Facet Reflectivity. <i>Optical and Quantum Electronics</i> , <b>2004</b> , 36, 443-457  | 2.4 |    |
| 46 | Investigation of Indium Tin Oxide (ITO) films for the VCSEL laser with dielectric Bragg reflectors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2004</b> , 1, 396-400   |     |    |
| 45 | Threshold simulation of 1.3- $\mu\text{m}$ oxide-confined in-plane quantum-dot (InGa)As/GaAs lasers. <i>Optical and Quantum Electronics</i> , <b>2003</b> , 35, 675-692  | 2.4 | 4  |
| 44 | Electron microscopy study of advanced heterostructures for optoelectronics. <i>Materials Chemistry and Physics</i> , <b>2003</b> , 81, 244-248   | 4-4 | 1  |
| 43 | Output power saturation in InAs/GaAs quantum dot lasers. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 1351-1354   |     | 4  |
| 42 | Photoreflectance Study of GaN/AlGaN Structures. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , <b>2003</b> , 491-494  |     | 5  |
| 41 | Investigations of optical properties of active regions in vertical cavity surface emitting lasers grown by MBE. <i>Thin Solid Films</i> , <b>2002</b> , 412, 107-113   | 2.2 | 4  |
| 40 | Photoluminescence mapping and angle-resolved photoluminescence of MBE-grown InGaAs/GaAs RC LED and VCSEL structures. <i>Thin Solid Films</i> , <b>2002</b> , 412, 114-121  | 2.2 | 9  |

|    |   |     |   |
|----|---|-----|---|
| 39 | Resonant Cavity Enhanced Photonic Devices. <i>Acta Physica Polonica A</i> , <b>2002</b> , 101, 105-118  | 0.6 | 3 |
| 38 | Long-wavelength strained-layer InGaAs/GaAs quantum-well lasers grown by molecular beam epitaxy. <i>Microwave and Optical Technology Letters</i> , <b>2001</b> , 29, 75-77   | 1.2 | 2 |
| 37 | Dual Contribution to the Stokes Shift in InGaN/GaN Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>2001</b> , 228, 111-114   | 1.3 | 9 |
| 36 | The influence of erbium on the physical properties of GaN crystals grown from N solution in Ga at high nitrogen pressure. <i>High Pressure Research</i> , <b>2000</b> , 18, 35-39   | 1.6 |   |
| 35 | MBE growth of planar microcavities with distributed Bragg reflectors. <i>Thin Solid Films</i> , <b>2000</b> , 367, 290-294  | 2.2 | 7 |
| 34 | Many-body effects in highly p-type modulation-doped GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As quantum wells. <i>Physical Review B</i> , <b>2000</b> , 61, 2794-2798   | 3.3 | 9 |
| 33 | Magneto-optical studies of highly p-type modulation-doped GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As quantum wells. <i>Physical Review B</i> , <b>2000</b> , 62, 15952-15961   | 3.3 | 2 |
| 32 | Formation of Dislocations in InGaAs/GaAs Heterostructures. <i>Physica Status Solidi A</i> , <b>1999</b> , 171, 275-282  |     | 5 |
| 31 | Optical Properties of p-Type Modulation Doped GaAs/AlGaAs Quantum Wells. <i>Physica Status Solidi (B): Basic Research</i> , <b>1998</b> , 210, 615-620  | 1.3 | 2 |
| 30 | Conductance noise of submicron wires in the regime of quantum Hall effect. <i>Physica B: Condensed Matter</i> , <b>1998</b> , 256-258, 69-73  | 2.8 | 4 |
| 29 | Transport and tunneling within a compressible electron liquid in wires and rings of GaAs/Al <sub>x</sub> Ga <sub>1-x</sub> As heterostructures. <i>Physical Review B</i> , <b>1998</b> , 58, 16252-16261  | 3.3 | 6 |
| 28 | Fermi-Edge Singularity in Luminescence Spectra of P-Type Modulation Doped AlGaAs/GaAs Quantum Wells. <i>Acta Physica Polonica A</i> , <b>1998</b> , 94, 265-270   | 0.6 |   |
| 27 | Interisland exciton migration and enhanced bound exciton recombination in an AlGaAs/GaAs quantum well structure grown by molecular beam epitaxy without growth interruptions at interfaces. <i>Semiconductor Science and Technology</i> , <b>1997</b> , 12, 1416-1421 | 1.8 | 2 |
| 26 | Theoretical Analysis of Optical Gain in Quantum Well Lasers Including Valence-Band Mixing Effect. <i>Acta Physica Polonica A</i> , <b>1997</b> , 92, 903-907  | 0.6 |   |
| 25 | Low Threshold Room Temperature AlGaAs/GaAs GRIN SCH SQW Lasers Grown by MBE. <i>Acta Physica Polonica A</i> , <b>1996</b> , 90, 847-850   | 0.6 |   |
| 24 | Fermi-Edge Singularity in Excitonic Spectra of Modulation Doped AlGaAs/GaAs Quantum Wells. <i>Acta Physica Polonica A</i> , <b>1996</b> , 90, 751-754   | 0.6 |   |
| 23 | Inter-Island Energy Transfer in AlGaAs/GaAs Quantum Wells Grown by Molecular Beam Epitaxy. <i>Acta Physica Polonica A</i> , <b>1996</b> , 90, 1007-1011   | 0.6 |   |
| 22 | Exciton dynamics in thin quantum wells grown by MBE. <i>Thin Solid Films</i> , <b>1995</b> , 267, 84-88   | 2.2 | 2 |

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|----|--|-----|-----|
| 21 | Identification of Residual Impurities in Si-Doped MBE Grown GaAs. <i>Acta Physica Polonica A</i> , <b>1995</b> , 88, 775-778   | 0.6 | 2   |
| 20 | Transmission electron microscopy study of the formation of a contamination layer on the surface of porous silicon. <i>Journal of Materials Science: Materials in Electronics</i> , <b>1994</b> , 5, 280-283                  | 2.1 |     |
| 19 | Whole wafer assessment of electronic materials by scanning photoluminescence and surface photovoltage. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , <b>1993</b> , 20, 186-189 | 3.1 | 1   |
| 18 | Visible Light Emission from Porous Silicon. <i>Acta Physica Polonica A</i> , <b>1992</b> , 82, 914-918   | 0.6 | 2   |
| 17 | Physical Principles of the Operation of Semiconductor Lasers <b>1991</b> , 11-69   |     |     |
| 16 | The Design and Basic Characteristics of Semiconductor Lasers <b>1991</b> , 107-198   |     |     |
| 15 | Response to [Comment on Native acceptor levels in Ga-rich GaAs][J. Appl. Phys. 65, 596 (1989)]. <i>Journal of Applied Physics</i> , <b>1990</b> , 67, 7619-7619  | 2.5 | 1   |
| 14 | Native acceptor levels in Ga-rich GaAs. <i>Journal of Applied Physics</i> , <b>1989</b> , 65, 596-599  | 2.5 | 45  |
| 13 | Acceptor-bound magnetic polarons in Cd <sub>1-x</sub> MnxTe. <i>Physical Review B</i> , <b>1988</b> , 38, 10512-10516  | 3.3 | 43  |
| 12 | Optical characterization of semi-insulating GaAs: Determination of the Fermi energy, the concentration of the midgap EL2 level and its occupancy. <i>Applied Physics Letters</i> , <b>1987</b> , 51, 511-513                 | 3.4 | 18  |
| 11 | Growth and characterization of high quality LPEE GaAs bulk crystals. <i>Journal of Crystal Growth</i> , <b>1987</b> , 85, 136-141  | 1.6 | 13  |
| 10 | Diamagnetic shift of exciton energy levels in GaAs-Ga <sub>1-x</sub> Al <sub>x</sub> As quantum wells. <i>Solid State Communications</i> , <b>1986</b> , 60, 669-673   | 1.6 | 24  |
| 9  | Growth and luminescence properties of GaSb single crystals. <i>Acta Physica Hungarica</i> , <b>1985</b> , 57, 303-308  |     | 1   |
| 8  | Crystal growth of GaP doped with nitrogen under high nitrogen pressure. <i>Journal of Crystal Growth</i> , <b>1985</b> , 72, 711-716   | 1.6 | 8   |
| 7  | Pulsed laser annealing of nitrogen-implanted GaP. <i>Materials Letters</i> , <b>1985</b> , 3, 141-144  | 3.3 | 1   |
| 6  | Concentration-dependent absorption and photoluminescence of n-type InP. <i>Journal of Applied Physics</i> , <b>1985</b> , 57, 521-530  | 2.5 | 174 |
| 5  | Stoichiometry changes in III-V compounds under ion bombardment. <i>Nuclear Instruments &amp; Methods in Physics Research</i> , <b>1983</b> , 209-210, 621-627  |     | 5   |
| 4  | Energy bands of ternary alloy semiconductors: Coherent-potential-approximation calculations. <i>Physical Review B</i> , <b>1983</b> , 28, 7105-7114  | 3.3 | 48  |



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|---|--|-----|----|
| 3 | Determination of the nitrogen doping of liquid phase epitaxy GaP and Ga <sub>x</sub> In <sub>1-x</sub> P alloys by optical absorption and photoluminescence. <i>Journal of Applied Physics</i> , <b>1983</b> , 54, 5358-5362 | 2.5 | 19 |
| 2 | The kinetics of Si incorporation in Ga melt for LPE growth of GaP doped with nitrogen from NH <sub>3</sub> . <i>Journal of Crystal Growth</i> , <b>1982</b> , 60, 434-440  | 1.6 |    |
| 1 | A novel technique for investigation of luminescence properties of Ga <sub>1-x</sub> In <sub>x</sub> P LPE layers with a small In content. <i>Journal Physics D: Applied Physics</i> , <b>1981</b> , 14, 127-134              | 3   |    |